





Laser Mixes

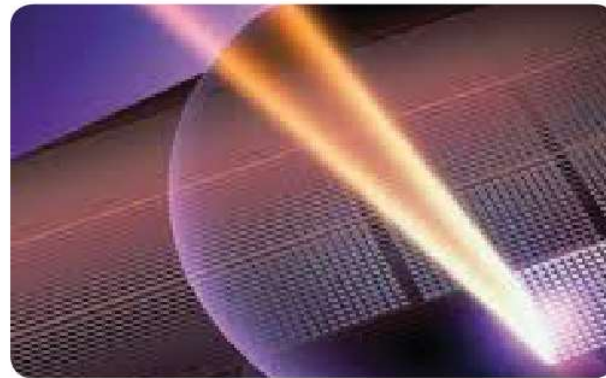
LASER MIX

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Laser mix gases are used for both Semiconductor(Excimer Laser Gas) and Display(Excimer Laser Annealing Gas). New filling facility and analyzer set up in Jeonui has been completed and it's total production capacity almost reaches 75,000 BT yearly.

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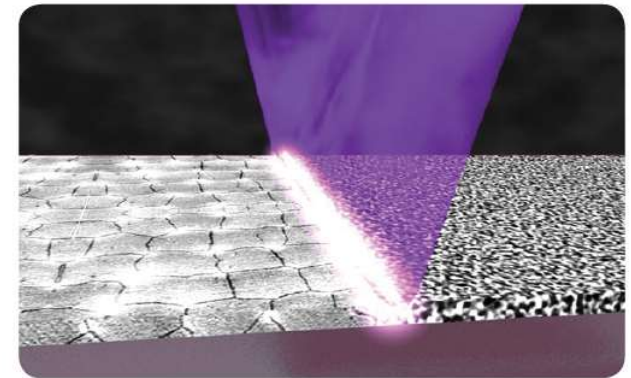
ELG: SEMI



Excimer Laser Gas
DRAM / Flash / Logic
Photo-Lithography

Item
3.5% Ar / 10ppmXe / Ne
0.95% F ₂ / 3.5% Ar / Ne
1.25% Kr / Ne
0.95% F ₂ / 1.25% Kr / Ne

ELA: DISPLAY



Excimer Laser Annealing Gas
LTPS / OLED
A-Si → Poly Si
LLO(Laser Lift Off):
Polyimide Off

Item
100ppm H ₂ / Ne
4.5%, 5% HCl Mix
O ₂ / Ne Mix
Xe
Ne



Jeonui Plant

PRODUCT LINE UP

	Product	Purity	Package		Manufacture type	Key para. (Impurity)
			Cylinder (L)	Valve type		
WMM Manufacture	NH3	5N5, 6N5, 7N	47, 440, ISO	DISS 720	Distillation	H2O, N2
	N2O	5N, 5N5	47, 440, ISO	CGA316, DISS 712	Synthesis, Distillation	H2O, N2
	C3H6	3N7	47	DISS 724	Purification	H2O, N2, OHC
	C4F8	5N	10, 47	JIS 22R	Purification	H2O, N2, OHC
	SF6	5N	47, 440	CGA590	Distillation	H2O, N2
	BF3	4N5	6.9, 47	DISS 642	Purification	H2O, N2, CO2
	He	6N	47	JIS 22R	Purification	H2O, N2
	PH3 Mix (0.1%, 1%, 10%, 15%)	6N	47, 440	CGA350, DISS 632	Blending & Mixing	Concentration
	F2 Mix (20%)	3N	47	JIS 22R	Blending & Mixing	Concentration
	BCl3 Mix (1%)	5N	47	DISS 634	Blending & Mixing	Concentration
	Xe	5N	47	CGA580	Purification	H2O, Kr
	3.5%Ar/ 10ppmXe/Ne	5N	44	CGA580	Blending & Mixing	Concentration
	0.95%F2/3.5%Ar/Ne	3N	44	CGA679	Blending & Mixing	Concentration
	1.25%Kr/Ne	5N	44	CGA580	Blending & Mixing	Concentration
	0.95%F2/1.25%Kr/Ne	3N	44	CGA679	Blending & Mixing	Concentration



THANK YOU